

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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# 2SA2080

Silicon PNP Epitaxial

**RENESAS**

ADE-208-1476 (Z)

Rev. 0  
Feb. 2002

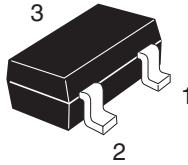
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## Features

- Low frequency amplifier

## Outline

CMPAK



1. Emitter
2. Base
3. Collector

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-30	V
Collector to emitter voltage	$V_{CEO}$	-30	V
Emitter to base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-100	mA
Emitter current	$I_E$	100	mA
Collector power dissipation	$P_C^*$	150	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +125	°C

\*Value on the glass epoxy board (10 mm x 10 mm x 0.7 mm)

## Electrical Characteristics

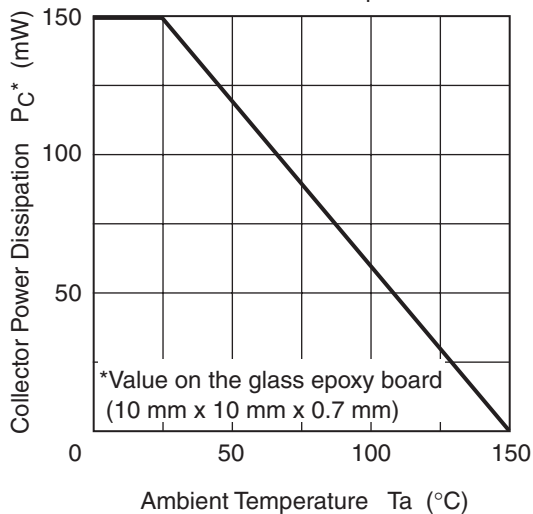
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-30	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-30	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	-0.5	$\mu A$	$V_{CB} = -20 \text{ V}, I_E = 0$
Emitter cutoff current	$I_{EBO}$	—	—	-0.5	$\mu A$	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	$h_{FE}^{*1}$	100	—	500	—	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.2	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$
Base to emitter voltage	$V_{BE}$	—	—	-0.75	V	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$

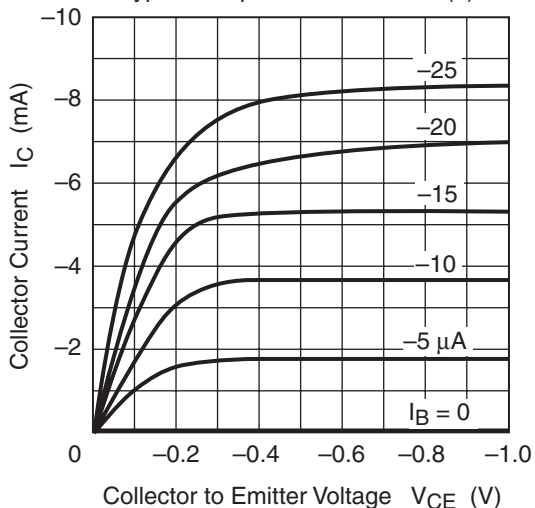
Notes: 1. The 2SA2080 is grouped by  $h_{FE}$  as follows.

Grade	B	C	D
Mark	MB	MC	MD
$h_{FE}$	100 to 200	160 to 320	250 to 500

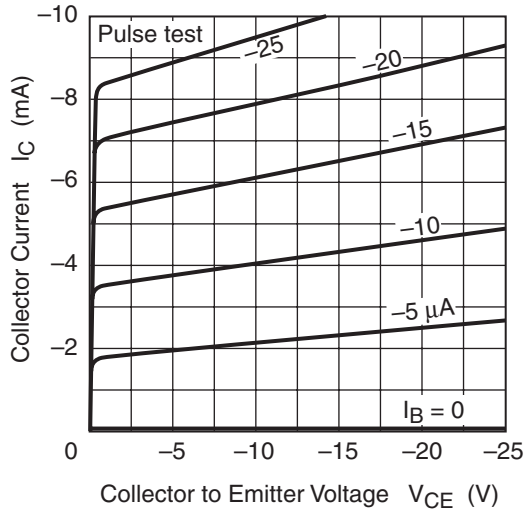
Maximum Collector Dissipation Curve



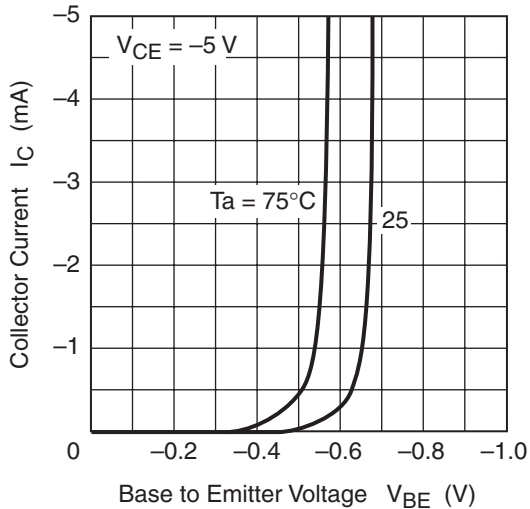
Typical Output Characteristics (1)



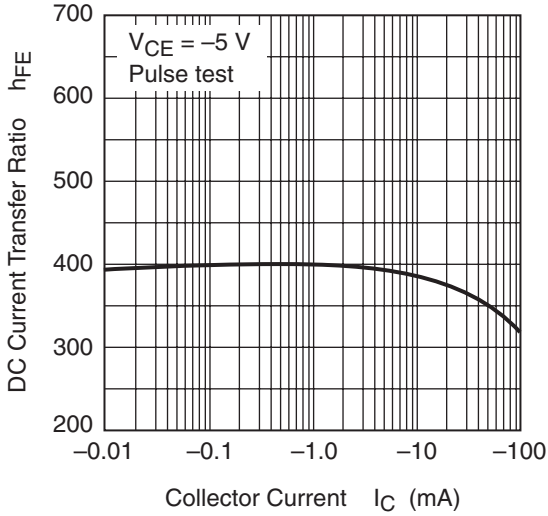
Typical Output Characteristics (2)



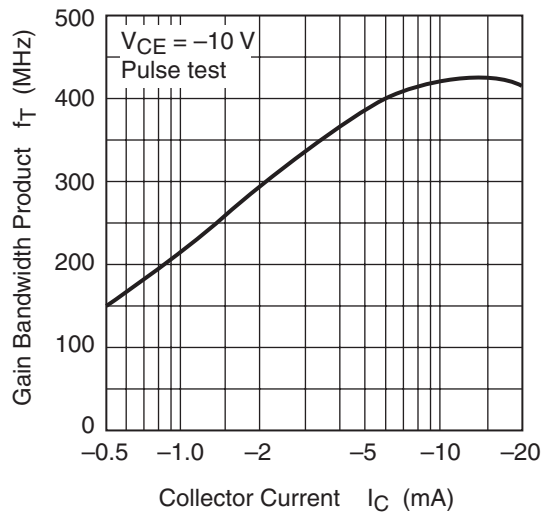
Typical Transfer Characteristics



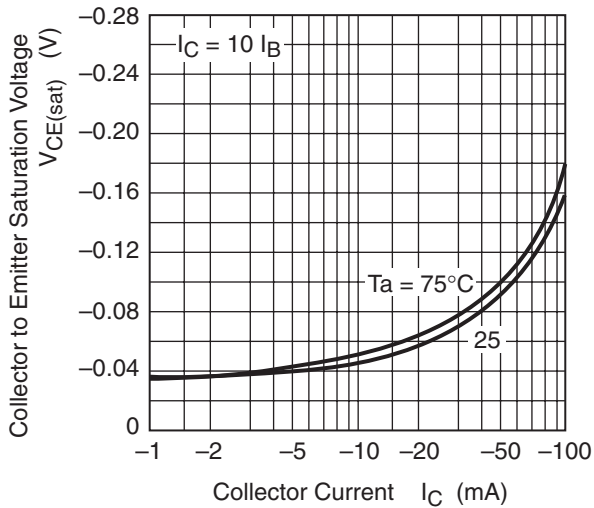
DC Current Transfer Ratio vs. Collector Current



Gain Bandwidth Product vs. Collector Current

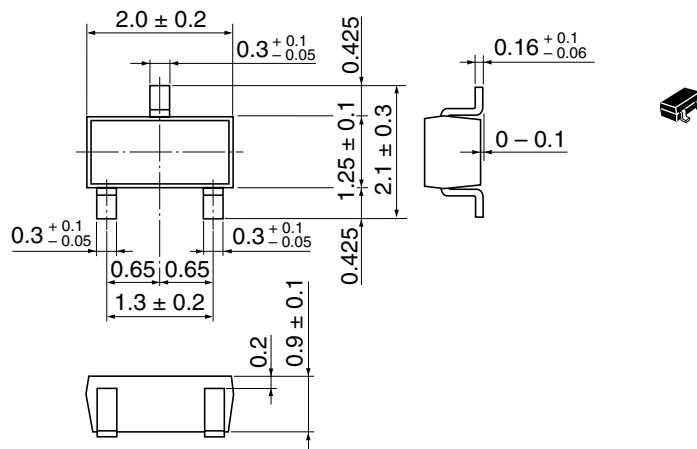


Collector to Emitter Saturation Voltage vs. Collector Current



## Package Dimensions

As of July, 2001  
Unit: mm



Hitachi Code	CMPAK
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.006 g

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**Sales Offices****HITACHI****Hitachi, Ltd.**

Semiconductor & Integrated Circuits  
 Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
 Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL <http://www.hitachisemiconductor.com/>

**For further information write to:**

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe Ltd. Electronic Components Group Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 585200	Hitachi Asia Ltd. Hitachi Tower 16 Collyer Quay #20-00 Singapore 049318 Tel : <65>-538-6533/538-8577 Fax : <65>-538-6933/538-3877 URL : <a href="http://semiconductor.hitachi.com.sg">http://semiconductor.hitachi.com.sg</a>	Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower World Finance Centre, Harbour City, Canton Road Tsim Sha Tsui, Kowloon Hong Kong Tel : <852>-(2)-735-9218 Fax : <852>-(2)-730-0281 URL : <a href="http://semiconductor.hitachi.com.hk">http://semiconductor.hitachi.com.hk</a>
	Hitachi Europe GmbH Electronic Components Group Dornacher StraÙe 3 D-85622 Feldkirchen Postfach 201, D-85619 Feldkirchen Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00	Hitachi Asia Ltd. (Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road Hung-Kuo Building Taipei (105), Taiwan Tel : <886>-(2)-2718-3666 Fax : <886>-(2)-2718-8180 Telex : 23222 HAS-TP URL : <a href="http://www.hitachi.com.tw">http://www.hitachi.com.tw</a>	

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